

## ● 硅 PNP 外延平面三极管

### ● 用途:

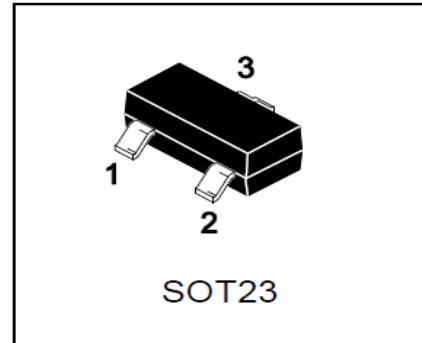
通用放大、开关

### ● 特点:

低电流

高电压

与 MMBT5551 构成互补对管



MARKING: 2L

PIN: 1、B, 2、E, 3、C

### ● 极限参数(Ta=25°C)

参数	符号	单位	规范值
耗散功率	P <sub>tot</sub>	mW	300
集电极电流	I <sub>c</sub>	mA	-500
结温	T(j)	°C	125
贮存温度	T <sub>stg</sub>	°C	-55~+125
集电极-基极电压	V <sub>CB0</sub>	V	-160
集电极-发射极电压	V <sub>CEO</sub>	V	-150
发射极-基极电压	V <sub>EBO</sub>	V	-5

### ● 电参数(Ta=25°C)

参数符号	测试条件	最小值	最大值	单位
V <sub>CB0</sub>	I <sub>C</sub> = -0.1mA I <sub>E</sub> = 0	-160		V
V <sub>CEO</sub>	I <sub>C</sub> = -1mA I <sub>B</sub> = 0	-150		V
V <sub>EBO</sub>	I <sub>E</sub> = -0.01mA I <sub>C</sub> = 0	-5		V
I <sub>CB0</sub>	V <sub>CB</sub> = -120V I <sub>E</sub> = 0		-50	nA
I <sub>EBO</sub>	V <sub>EB</sub> = -3V I <sub>C</sub> = 0		-50	nA
H <sub>FE</sub>	V <sub>CE</sub> = -5V I <sub>C</sub> = -10 mA	100	350	
V <sub>CE(sat)</sub>	I <sub>C</sub> = -50mA I <sub>B</sub> = -5mA		-0.5	V
V <sub>BE(sat)</sub>	I <sub>C</sub> = -50mA I <sub>B</sub> = -5mA		-1	V
f <sub>T</sub>	V <sub>CE</sub> = -5V I <sub>C</sub> = -10mA f = 30MHz	100		MHz

●  $H_{FE}$  分档

Rank	L	H
$H_{FE}$	100-250	220-350

● 典型曲线图

Fig.1 Collector Output Capacitance

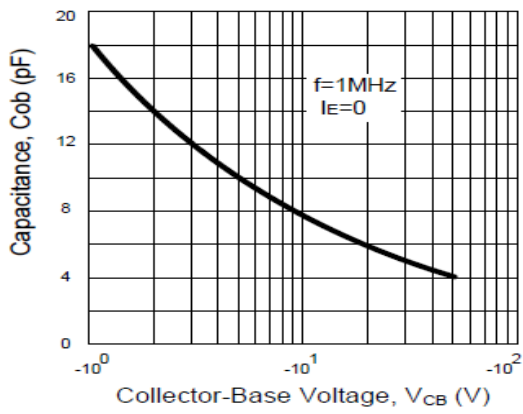


Fig.2 DC Current Gain

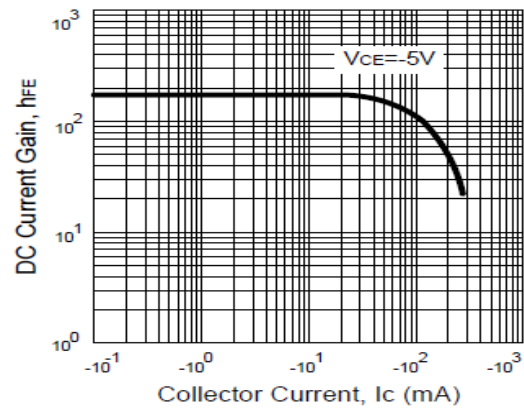


Fig.3 Base-Emitter on Voltage

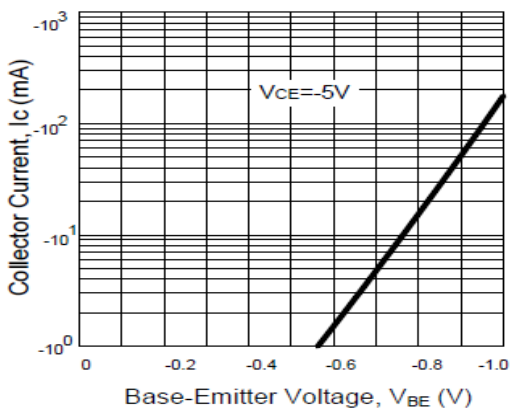


Fig.4 Saturation Voltage

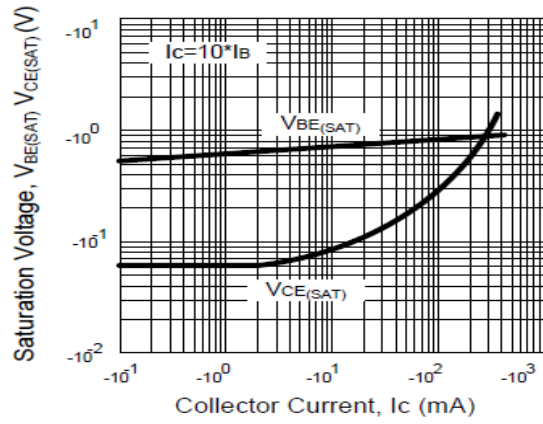
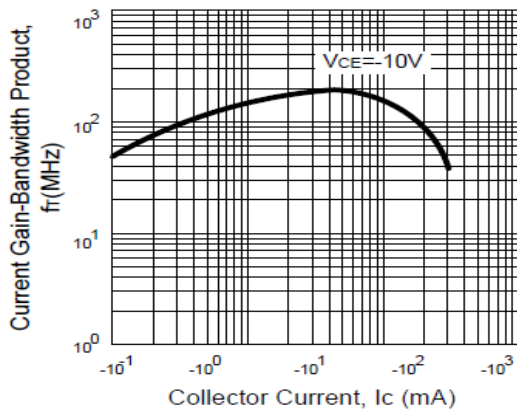
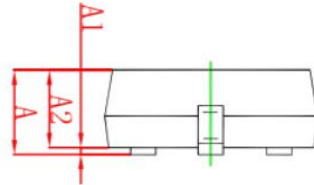
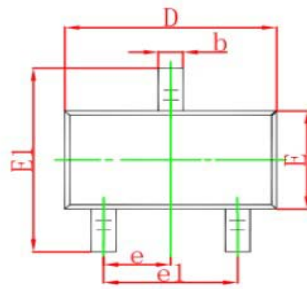


Fig.5 Current Gain-Bandwidth Product



●SOT-23 封装外形尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°